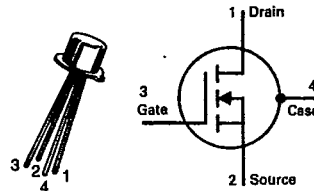


**3N169
thru
3N171****CASE 20-03, STYLE 2
TO-72 (TO-206AF)****MOSFETs
SWITCHING****N-CHANNEL — ENHANCEMENT**

Refer to 2N4351 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	25	Vdc
Drain-Gate Voltage	V_{DG}	± 35	Vdc
Gate-Source Voltage	V_{GS}	± 35	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 1.7	mW mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	800 4.56	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	-65 to +175	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage ($I_D = 10 \mu\text{Adc}$, $V_{GS} = 0$)	$V_{(BR)DSX}$	25	—	Vdc
Zero-Gate-Voltage Drain Current ($V_{DS} = 10 \text{ Vdc}$, $V_{GS} = 0$) ($V_{DS} = 10 \text{ Vdc}$, $V_{GS} = 0$, $T_A = 125^\circ\text{C}$)	I_{DSS}	—	10 1.0	nAdc μAdc
Gate Reverse Current ($V_{GS} = -35 \text{ Vdc}$, $V_{DS} = 0$) ($V_{GS} = -35 \text{ Vdc}$, $V_{DS} = 0$, $T_A = 125^\circ\text{C}$)	I_{GSS}	—	10 100	pAdc
ON CHARACTERISTICS				
Gate Threshold Voltage ($V_{DS} = 10 \text{ Vdc}$, $I_D = 10 \mu\text{Adc}$)	$V_{GS(Th)}$	0.5 1.0 1.5	1.5 2.0 3.0	Vdc
Drain-Source On-Voltage ($I_D = 10 \text{ mAdc}$, $V_{GS} = 10 \text{ Vdc}$)	$V_{DS(on)}$	—	2.0	Vdc
On-State Drain Current ($V_{GS} = 10 \text{ Vdc}$, $V_{DS} = 10 \text{ Vdc}$)	$I_{D(on)}$	10	—	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Drain-Source Resistance ($V_{GS} = 10 \text{ Vdc}$, $I_D = 0$, $f = 1.0 \text{ kHz}$)	$r_{ds(on)}$	—	200	Ohms
Forward Transfer Admittance ($V_{DS} = 10 \text{ Vdc}$, $I_D = 2.0 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	$ y_{fs} $	1000	—	μmhos
Input Capacitance ($V_{DS} = 10 \text{ Vdc}$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{iss}	—	5.0	pF
Reverse Transfer Capacitance ($V_{DS} = 0$, $V_{GS} = 0$, $f = 1.0 \text{ MHz}$)	C_{rss}	—	1.3	pF
Drain-Substrate Capacitance ($V_{D(SUB)} = 10 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	$C_{d(sub)}$	—	5.0	pF
SWITCHING CHARACTERISTICS				
Turn-On Delay Time	$t_{d(on)}$	—	3.0	ns
Rise Time	t_r	—	10	ns
Turn-Off Delay Time	$t_{d(off)}$	—	3.0	ns
Fall Time	t_f	—	15	ns

MOTOROLA SMALL-SIGNAL TRANSISTORS, FETs AND DIODES

T-3525

FIGURE 1 — SWITCHING TIME TEST CIRCUIT

